P-Channel Enhancement Mode MOSFET

MTP2305N3

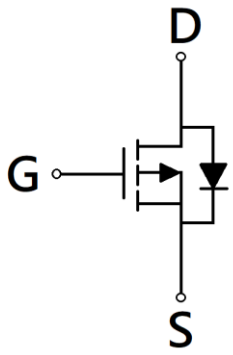
Features

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic

BV_{DSS}	-20V
I_D@V_{GS}=-4.5V, T_A=25°C	-4.5A
$R_{DS(ON)\ typ.}$@ V_{GS}=-4.5V, I_D=-4.5A	35mΩ
$R_{DS(ON)\ typ.}$@ V_{GS}=-2.5V, I_D=-2A	45mΩ
$R_{DS(ON)\ typ.}$@ V_{GS}=-1.8V, I_D=-1A	65mΩ

Equivalent Circuit

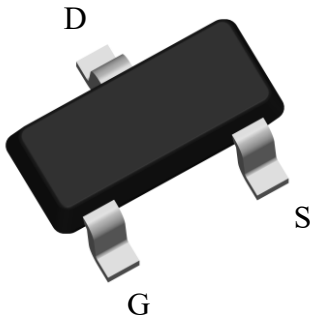
MTP2305N3



G : Gate S : Source D : Drain

Outline

SOT-23



Ordering Information

Device	Package	Shipping
MTP2305N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products

Packing spec, T1 : 3000 pcs / tape & reel,7" reel

Product rank, zero for no rank products

Product name

Absolute Maximum Ratings (T_A=25°C)

Parameter			Symbol	Limits	Unit
Drain-Source Voltage			V_{DS}	-20	V
Gate-Source Voltage			V_{GS}	±8	
Continuous Drain Current @ V_{GS}=-4.5V, T_A=25°C		*a	I_D	-4.5	A
Continuous Drain Current @ V_{GS}=-4.5V, T_A=70°C		*a		-3.6	
Pulsed Drain Current		*b	I_{DM}	-18	
Continuous Body Diode Forward Current @ T_A=25°C		*a	I_S	-1	
Total Power Dissipation	T_A=25°C	*a	P_D	1.4	W
	T_A=70°C	*a		0.9	
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55~+150	°C

Thermal Data

Parameter		Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	*a	$R_{\theta JA}$	90	°C/W

Note:

*a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_D is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

*b. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

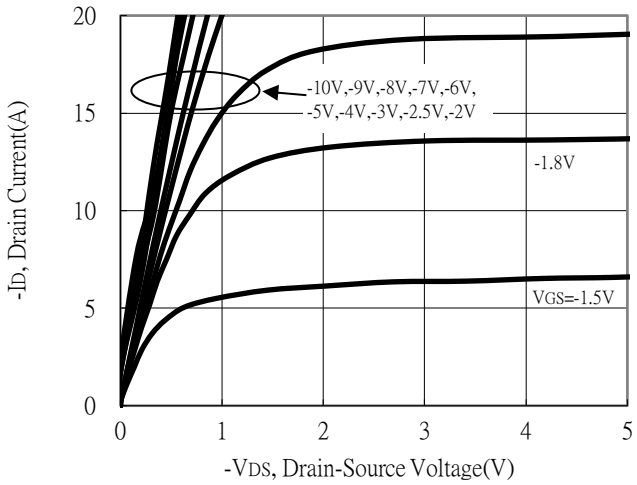
Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-20	-	-	V	V_{GS}=0V, I_D=-250μA
$V_{GS(th)}$	-0.4	-	-1.4		V_{DS}=V_{GS}, I_D=-250μA
G_{FS}	-	9	-	S	V_{DS}=-10V, I_D=-4.5A
I_{GSS}	-	-	±100	nA	V_{GS}=±8V, V_{DS}=0V
I_{DSS}	-	-	-1	μA	V_{DS}=-16V, V_{GS}=0V
$R_{DS(ON)}$	-	35	45	mΩ	V_{GS}=-4.5V, I_D=-4.5A
	-	45	60		V_{GS}=-2.5V, I_D=-2A
	-	65	120		V_{GS}=-1.8V, I_D=-1A
Dynamic					
Ciss	-	1150	-	pF	V_{DS}=-10V, V_{GS}=0V, f=1MHz
Coss	-	120	-		
Crss	-	105	-		
Rg	-	25	-	Ω	f=1MHz
Qg *1, 2	-	14	-	nC	V_{DS}=-10V, I_D=-4.5A, V_{GS}=-4.5V
Qgs *1, 2	-	1.7	-		
Qgd *1, 2	-	3.5	-		
$t_{d(ON)}$ *1, 2	-	5	-	ns	V_{DS}=-10V, I_D=-4.5A, V_{GS}=-4.5V, R_{GS}=1Ω
tr *1, 2	-	17	-		
$t_{d(OFF)}$ *1, 2	-	112	-		
t_f *1, 2	-	145	-		
Source-Drain Diode					
V_{SD} *1	-	-0.85	-1.2	V	I_S=-4.5A, V_{GS}=0V
trr	-	68	-	ns	I_F=-4.5A, dI_F/dt=100A/μs
Qrr	-	62	-	nC	

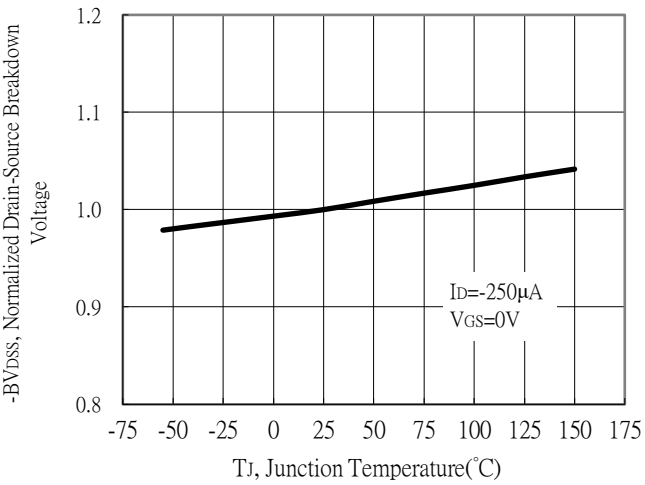
Note:
*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
*2. Independent of operating temperature

Typical Characteristics

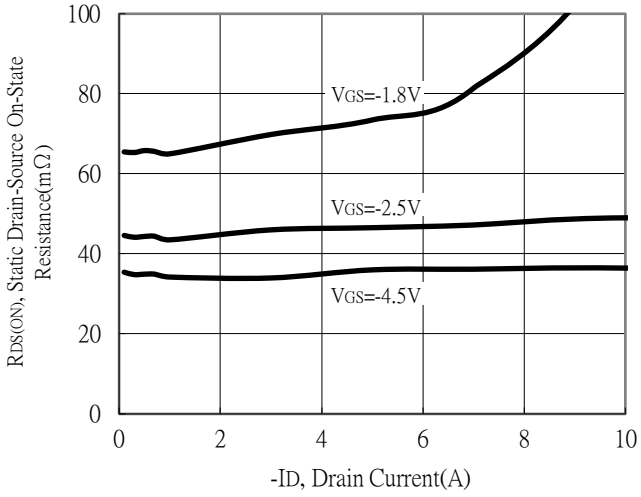
Typical Output Characteristics



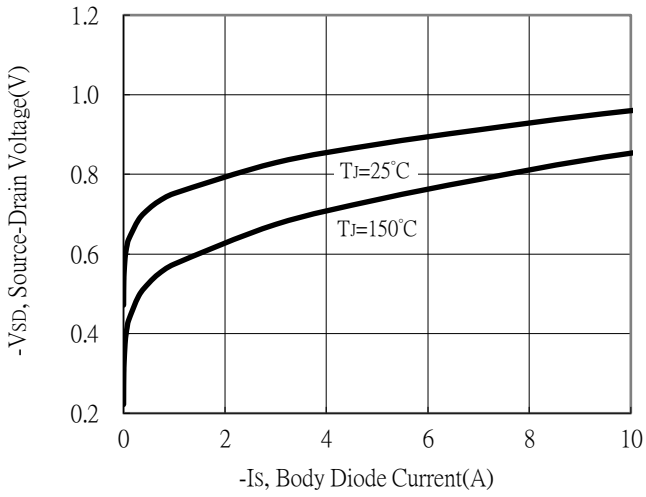
Breakdown Voltage vs Ambient Temperature



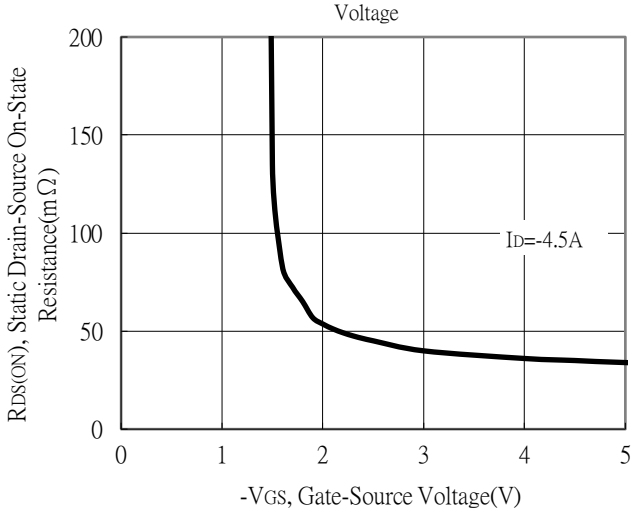
Static Drain-Source On-State resistance vs Drain Current



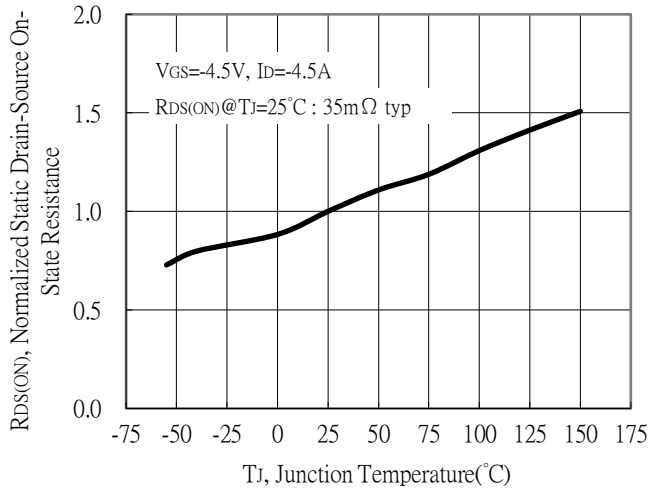
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

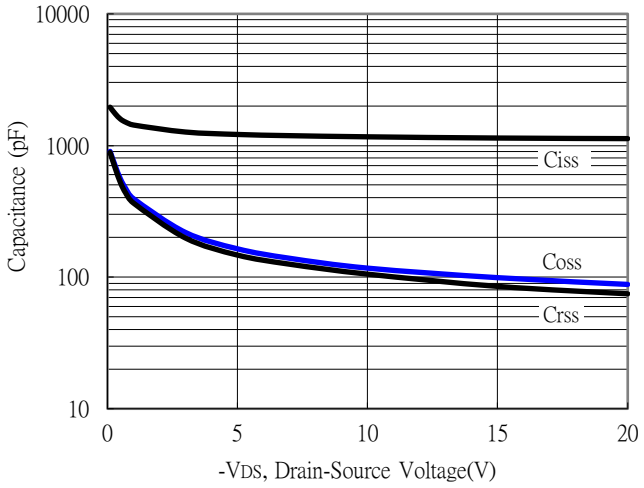


Drain-Source On-State Resistance vs Junction Temperature

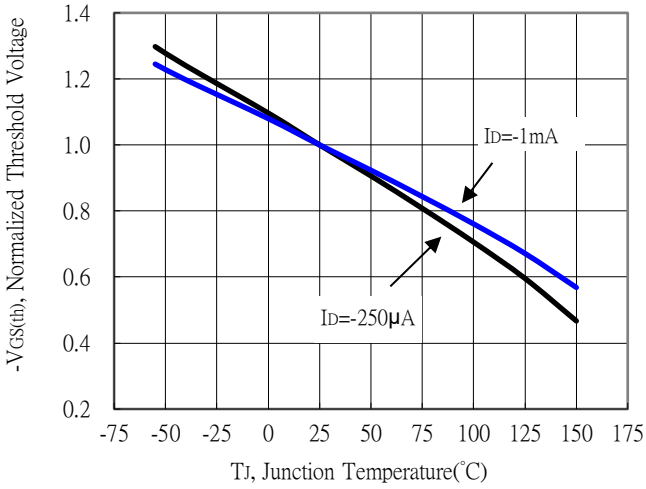


Typical Characteristics (Cont.)

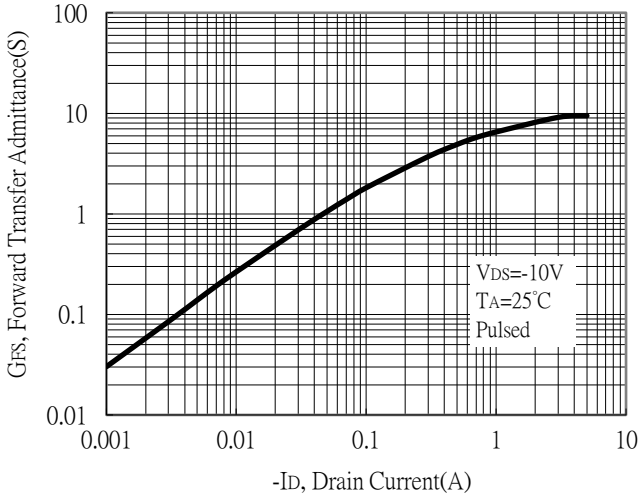
Capacitance vs Drain-to-Source Voltage



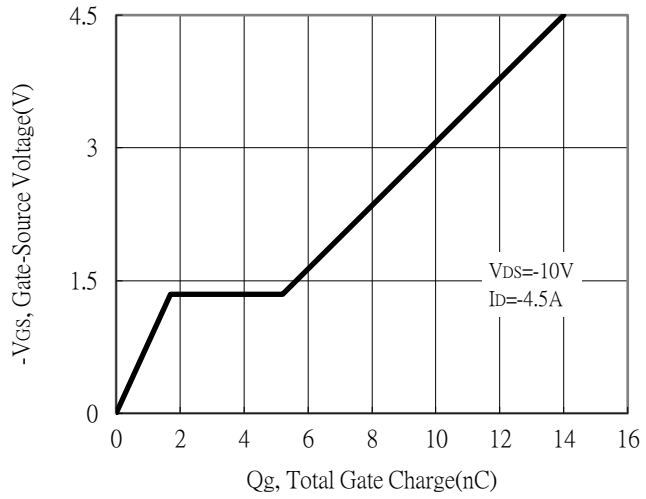
Threshold Voltage vs Junction Temperature



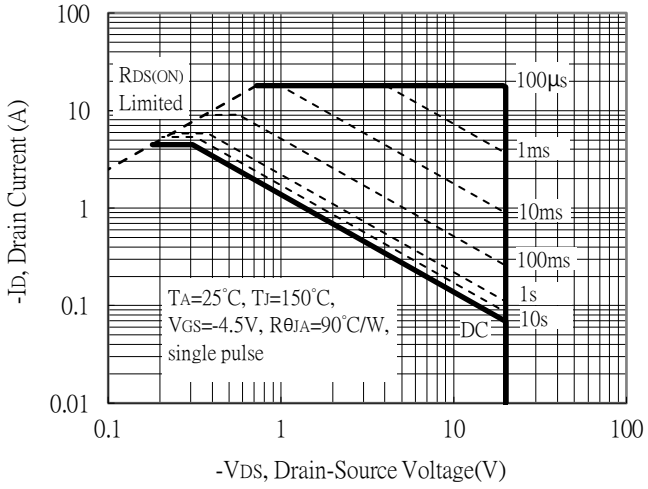
Forward Transfer Admittance vs Drain Current



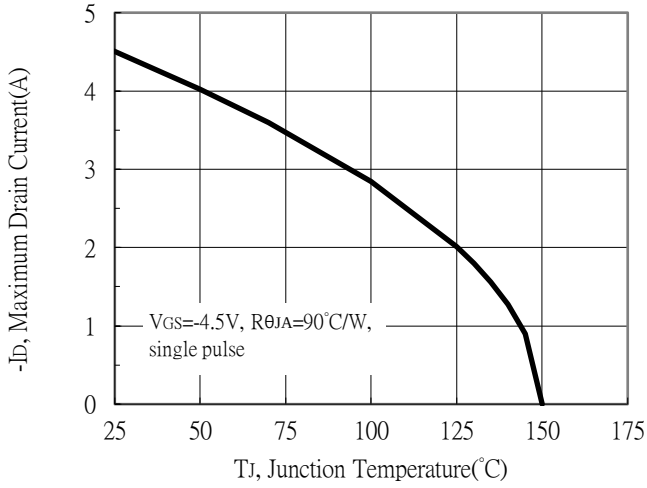
Gate Charge Characteristics



Maximum Safe Operating Area

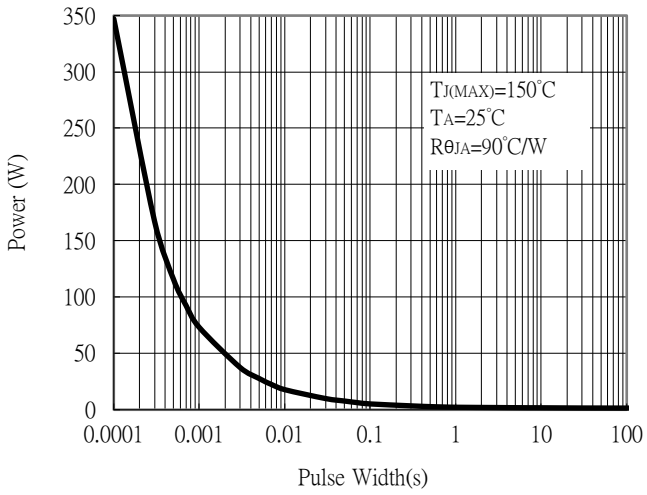


Maximum Drain Current vs Junction Temperature

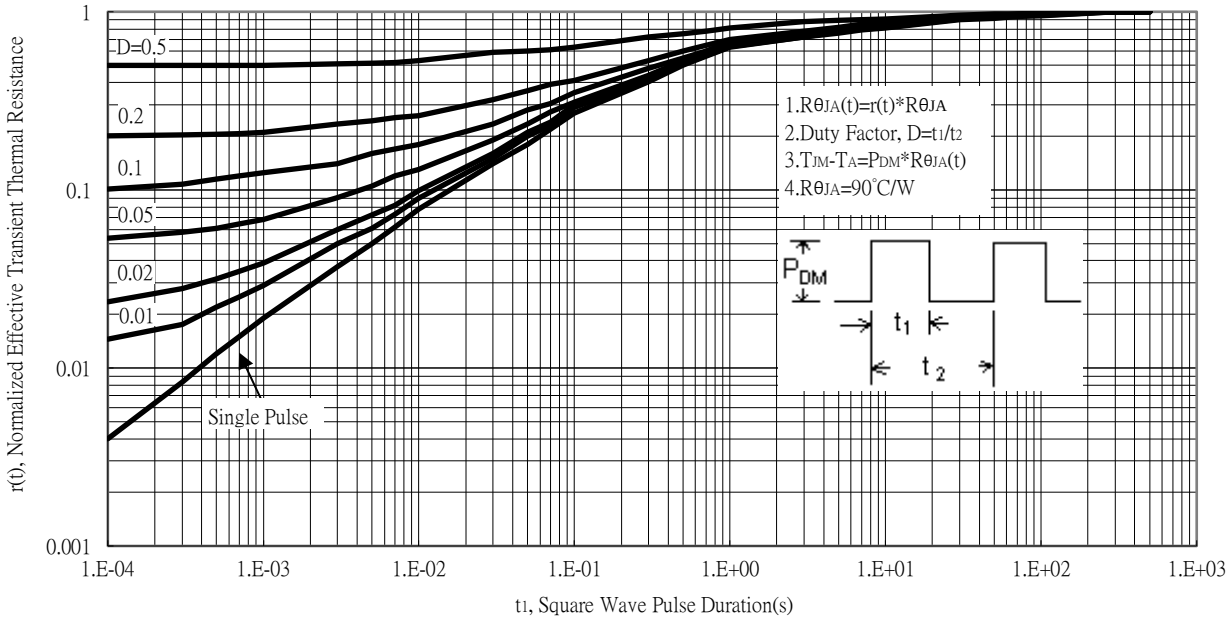


Typical Characteristics (Cont.)

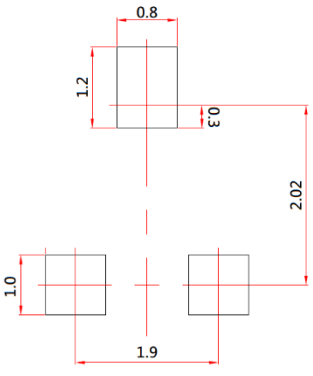
Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves

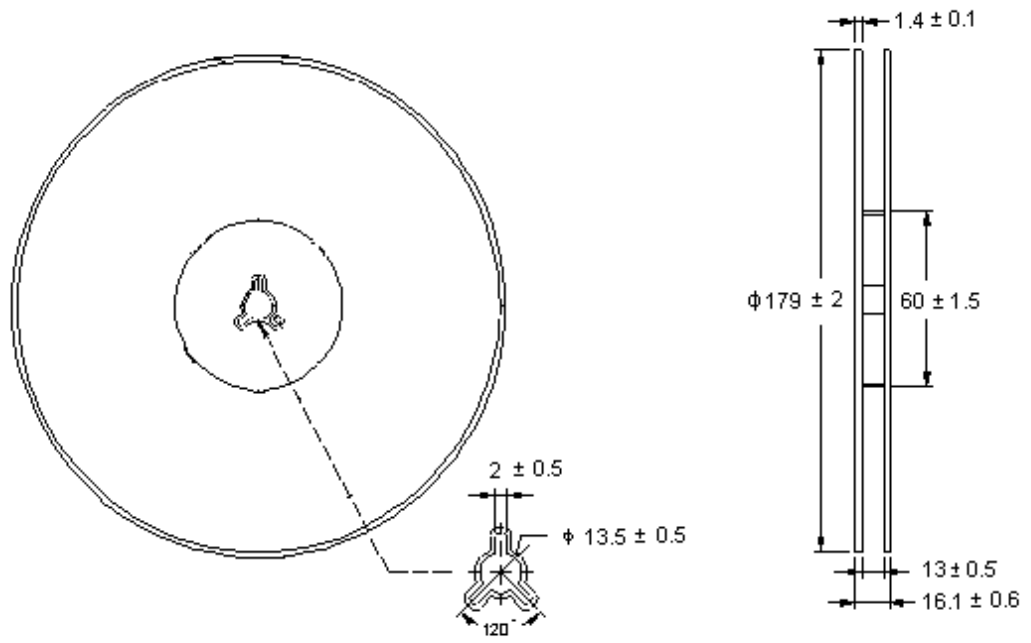


Recommended Soldering Footprint



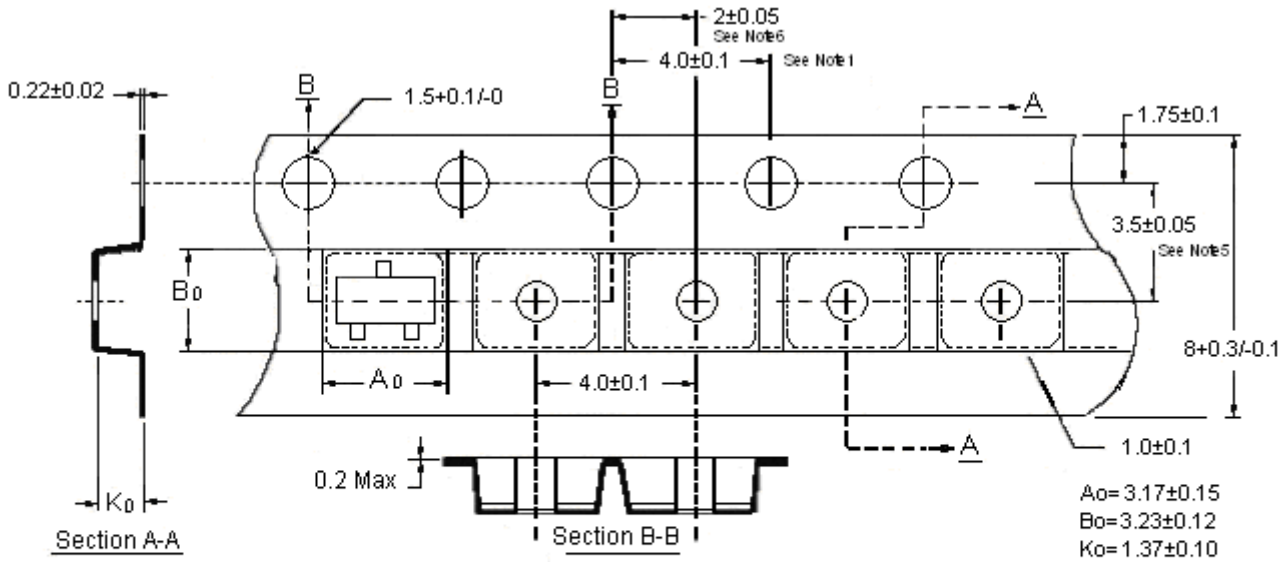
Unit : mm

Reel Dimension



Unit: millimeter

Carrier Tape Dimension



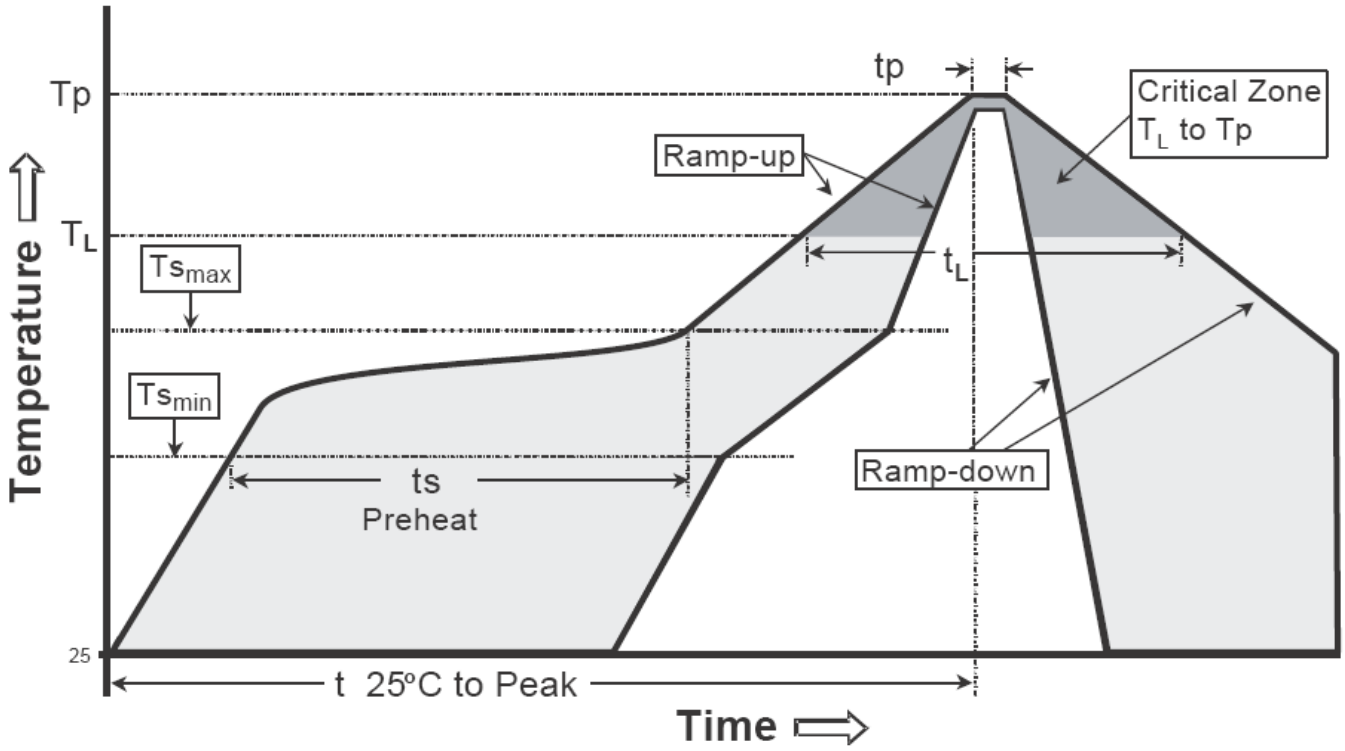
Notes:
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

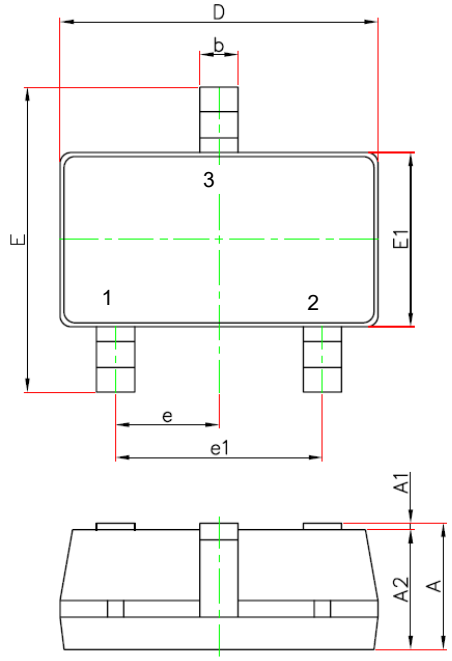
Recommended temperature profile for IR reflow

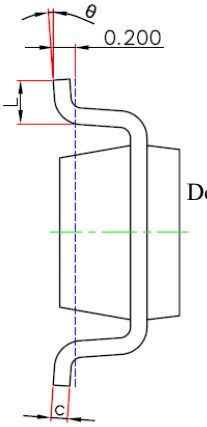


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(Ts min) −Temperature Max(Ts max) −Time(ts min to ts max)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (TL) − Time (tL)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

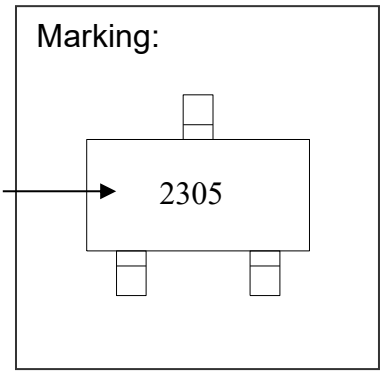
Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension





Device Code



Style: Pin 1.Gate 2.Source 3.Drain

3-Lead SOT-23 Plastic
Surface Mounted Package
CYStek Package Code: N3

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.035	0.049	0.90	1.25	E1	0.047	0.067	1.20	1.70
A1	0.000	0.004	0.00	0.10	E	0.089	0.116	2.25	2.95
A2	0.041	0.045	1.05	1.15	e	0.037 BSC		0.95 BSC	
b	0.012	0.020	0.30	0.50	e1	0.071	0.079	1.80	2.00
c	0.003	0.008	0.08	0.20	L	0.012	0.024	0.30	0.60
D	0.110	0.119	2.80	3.02	θ	0°	8°	0°	8°

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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